

Fig. 1 (a)

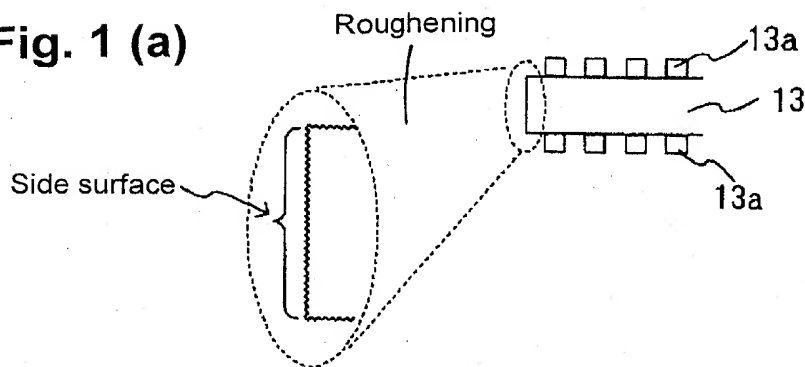


Fig. 1 (b)

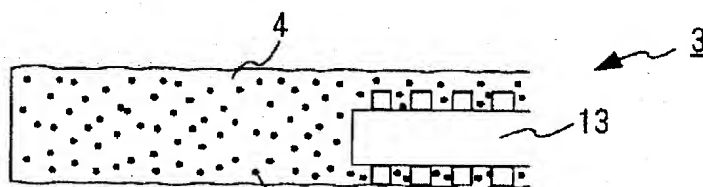


Fig. 1 (c)

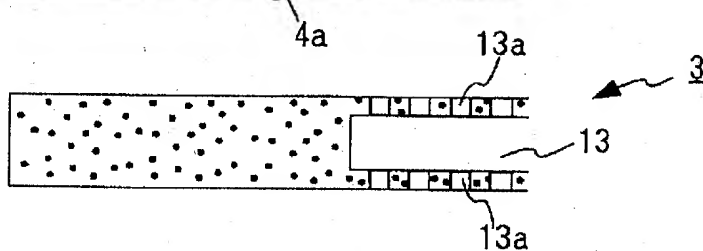


Fig. 1 (d)

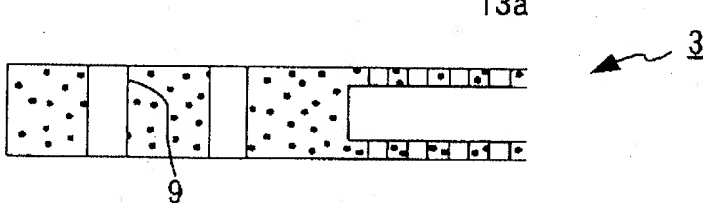


Fig. 1 (e)

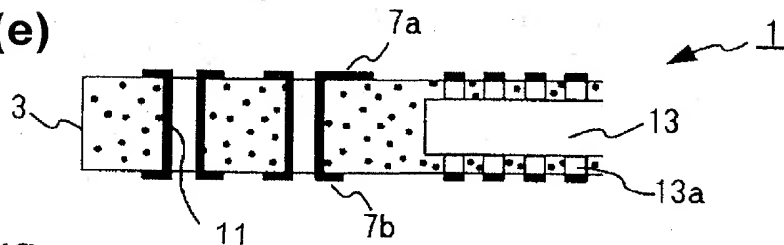
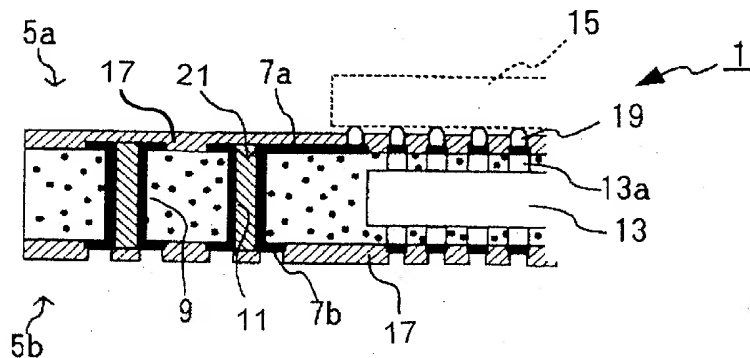


Fig. 1 (f)



This cross-sectional view shows a semiconductor device 1. It features a substrate 11 with a base layer 5a on top. A patterned layer 7a is formed on the base layer 5a. Within the substrate 11, there are three rectangular regions 3, each containing a pattern of dots. These regions are separated by vertical walls 103. Above the base layer 5a, there is a layer 109. On the right side, there is a series of rounded structures 111. Below the base layer 5a, there is a layer 107b. A dashed line 15 indicates a boundary or interface. Other labels include 105a, 105b, 7b, 21, 107a, and 13.

Fig. 3 (a)

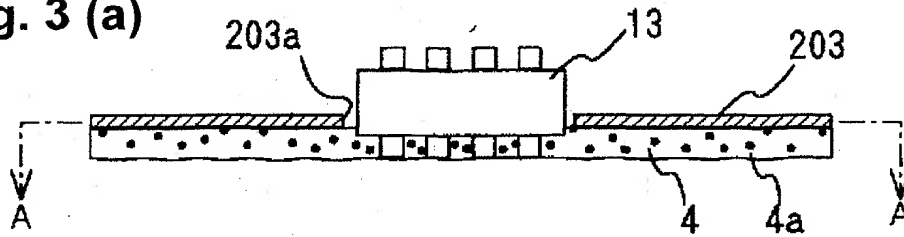


Fig. 3 (b)

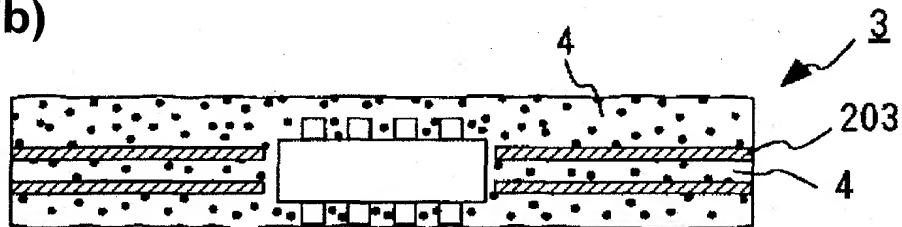
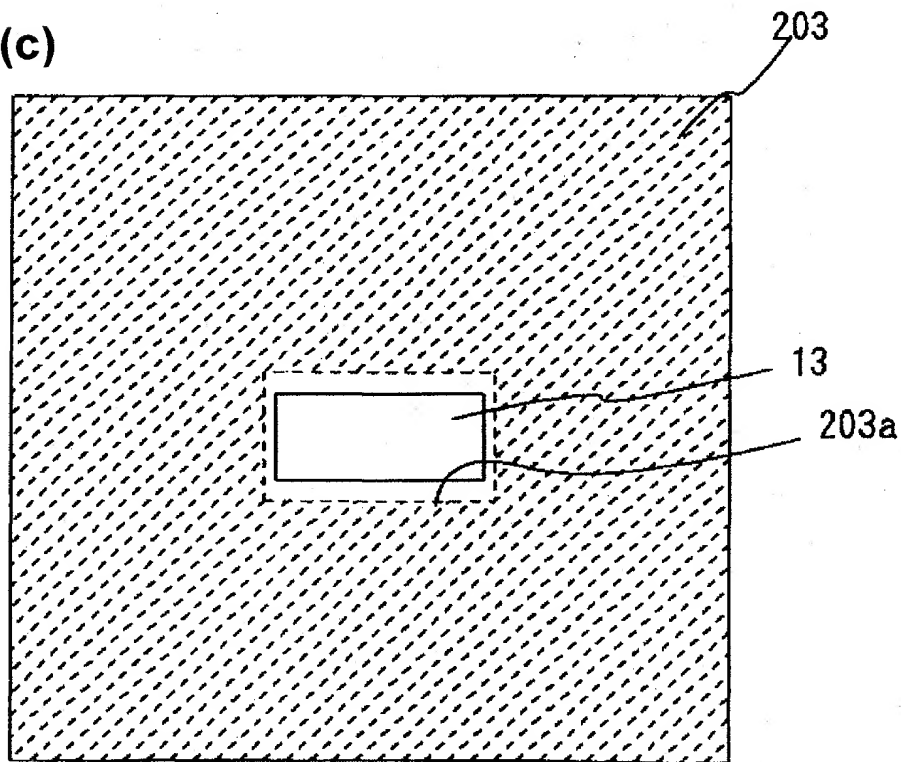


Fig. 3 (c)



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Fig. 4

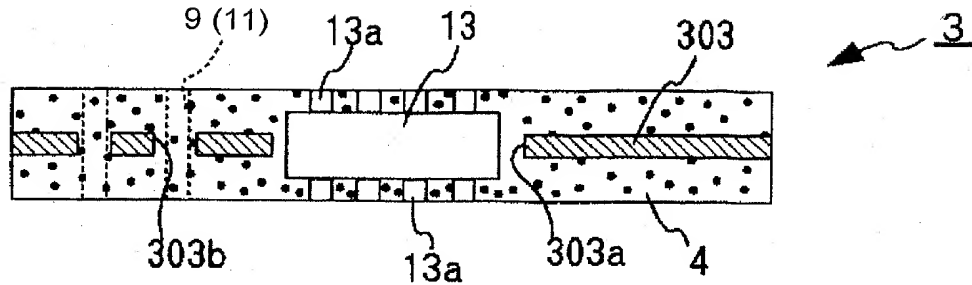


Fig. 5(a)

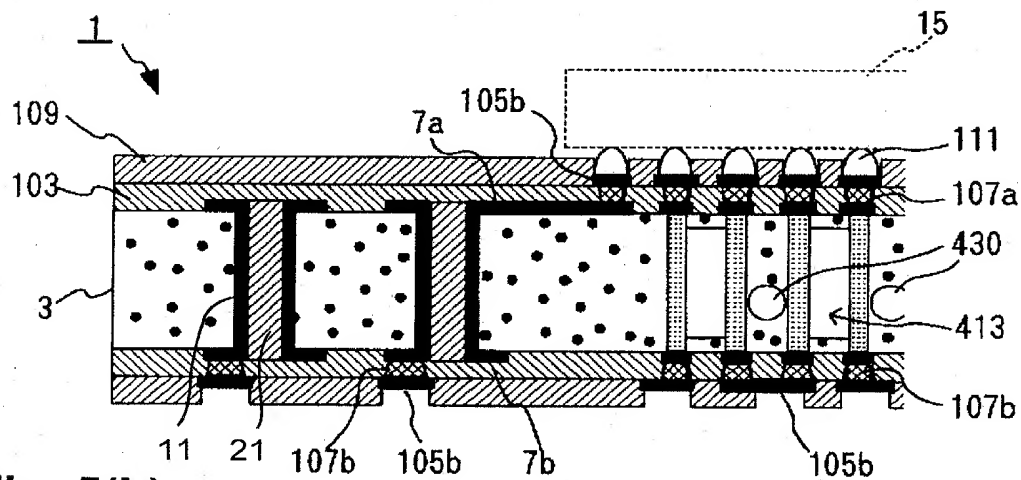


Fig. 5(b)

